20 GHz GaAs IMPATT Diode Development for Solid State Transmitter

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M.J. Delaney, M.H. Jones and C. Sun. "20 GHz GaAs IMPATT Diode Development for Solid State Transmitter." 1985 MTT-S International Microwave Symposium Digest 85.1 (1985 [MWSYM]): 525-527.

Double drift Read GaAs IMPATT diodes were fabricated for K Band from high quality MBE material. Single diode oscillator performance of 4.36w output and 19% efficiency were obtained at the flange of a reduced height cavity. A maximum power of 5.37W was obtained at a reduced efficiency.

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